TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC4S69F

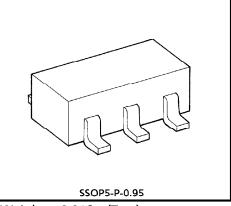
INVERTER GATE

The TC4S69F is three stage inverter.

The output is provided with the buffer, the input/output voltage characteristic has been improved. Thus an increase in propagation delay time caused by an increase in load capacity is kept to a minimum.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	V_{DD}	$V_{SS} - 0.5 \sim V_{SS} + 20$	V
Input Voltage	V _{IN}	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	٧
Output Voltage	VOUT	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	٧
DC Input Current	IN	± 10	mA
Power Dissipation	PD	200	mW
Operating Temperature Range	T _{opr}	− 40~85	°C
Storage Temperature Range	T _{stg}	- 65~150	°C
Lead Temperature (10s)	TL	260	°C

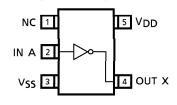


Weight: 0.016g (Typ.)

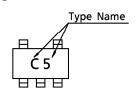
LOGIC DIAGRAM

IN A O OUT X

PIN CONFIGURATION (TOP VIEW)



MARKING



961001EBA2

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RECOMMENDED OPERATING CONDITIONS $(V_{SS} = 0V)$

CHARACTERISTIC	SYMBOL		MIN.	TYP.	MAX.	UNIT
DC Supply Voltage	V_{DD}	_	3	_	18	V
Input Voltage	V _{IN}		0	_	V_{DD}	V

STATIC ELECTRICAL CHARACTERISTICS $(V_{SS} = 0V)$

CHARACTERISTIC S		TEST CONDITION	V_{DD}	– 40°C		25°C			85°C		UNIT
BOL	BOL	TEST CONDITION	(V)	MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High-Level Output Voltage	V _{ОН}	l _{OUT} >1μΑ V _{IN} =V _{SS}	5 10	4.95 9.95	_	4.95 9.95	10.00	_	4.95 9.95	_	
Satpat voltage	11N - +22	15	14.95		14.95			14.95		V	
Low-Level Output Voltage	 l _{OUT} <1μΑ	5	_	0.05	_	0.00		—	0.05	-	
	VOL	$V_{IN} = V_{DD}$	10 15		0.05 0.05		0.00	l	_	0.05 0.05	
		V _{OH} = 4.6V	5	- 0.61	_	- 0.51	- 1.0	_	- 0.42	_	
Output High		V _{OH} = 2.5V	5	- 2.5	_	- 2.1	- 4.0	_	- 1.7	_	
Output High Current	ЮН	V _{OH} = 9.5V	10	- 1.5	_	- 1.3	- 2.2	—	- 1.1	_	
Current		V _{OH} = 13.5V	15	- 4.0	_	- 3.4	- 9.0	—	- 2.8	_	
		$V_{IN} = V_{SS}$							•		mA
		$V_{OL} = 0.4V$	5	0.61		0.51		l .	0.42	_	IIIA
Output Low	lOL	V _{OL} = 0.5V	10	1.5		1.3		i	1.1	i e	
Current	'OL	V _{OL} = 1.5V	15	4.0	_	3.4	12.0	—	2.8	_	
		$V_{IN} = V_{DD}$									
		V _{OUT} = 0.5V	5	3.5	_	3.5			3.5	_	
Input High Voltage	V _{IH}	V _{OUT} = 1.0V	10	7.0		7.0			7.0		
Imput mgn voltage	* IH	V _{OUT} = 1.5V	15	11.0	_	11.0	8.25	—	11.0	_	
		l _{OUT} <1μΑ									V
	VIL	V _{OUT} = 4.5V	5	—	1.5	—	2.25	l .	—	1.5	V
Input Low Voltage		V _{OUT} = 9.0V	10	_	3.0	_	4.5	l	 	3.0	
	* L	V _{OUT} = 13.5V	15	_	4.0	_	6.75	4.0	-	4.0	
		l _{OUT} <1μΑ									
Input H Level	ΊΗ	V _{IH} = 18V	18	_	0.1	_	10 ⁻⁵		_	1.0	μΑ
Current L Level	կլ	V _{IL} = 0V	18	_	- 0.1		- 10 ⁻⁵		_	- 1.0	μΑ
Quiescent Device Current	l _{DD}		5		0.25	_	0.001	l	-	7.5	
		$V_{IN} = V_{SS}$, V_{DD}	10	_	0.5	_	0.001	l	—	15	μ A
			15	_	1.0	_	0.002	1.0	_	30	

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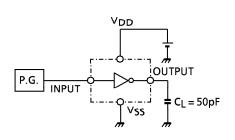
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DYNAMIC ELECTRICAL CHARACTERISTICS (Ta = 25°C, V_{SS} = 0V, C_L = 50pF)

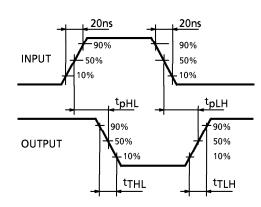
CHARACTERISTIC	SYMBOL	TEST CONDITION VDD (V)		MIN.	TYP.	MAX.	UNIT
Output Transition Time			5	_	70	200	
Output Transition Time	tTLH	_	10	_	35	100	
(Low to High)			15	_	30	80	
Output Transition Time (High to Low)			5	_	70	200	ns
	tTHL	<u> </u>	10	_	35	100	
			15	_	30	80	
	t _{pLH}		5	_	65	200	
Propagation Delay Time		<u> </u>	10	_	30	100	
			15	_	25	80	
	t _{pHL}		5	_	65	200	ns
Propagation Delay Time		_	10	_	30	100	
			15	_	25	80	
Input Capacitance	CIN	_	_	5	7.5	pF	

CIRCUIT AND WAVEFORM FOR MEASUREMENT OF DYNAMIC CHARACTERISTICS

TEST CIRCUIT



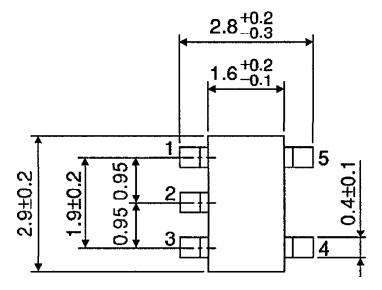
WAVEFORM

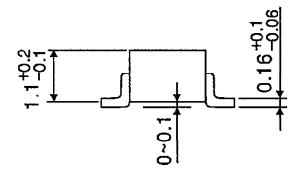


OUTLINE DRAWING

SSOP5-P-0.95

Unit: mm





Weight: 0.016g (Typ.)